

# Surface Mount RF Schottky Detector Diodes in SOT-363 (SC-70, 6 Lead)

## Technical Data

### HSMS-285L/P HSMS-286K/L/P/R

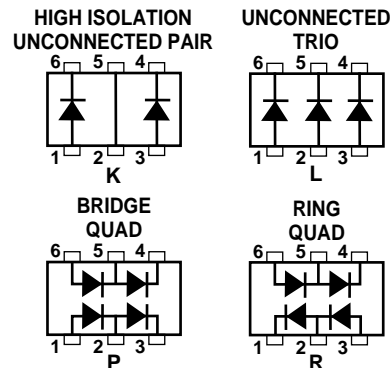
#### Features

- **Unique configurations in surface mount SOT-363 package**
  - increase flexibility
  - save board space
  - reduce cost
- **Excellent sensitivity for better detection**
  - HSMS-286a for higher frequencies
  - HSMS-285a zero bias for less power consumption
- **HSMS-286K grounded center leads provide up to 10 dB higher isolation**
- **Matched diodes for consistent performance**
- **Better thermal conductivity for higher power dissipation**

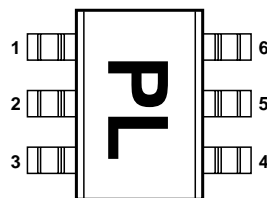
#### Applications

Both are ideal for RF/ID and RF Tag; cellular and other consumer applications requiring small and large signal detection; modulation; RF to DC conversion; or voltage doubling.

#### Package Lead Code Identification (Top View)



#### Pin Connections and Package Marking



#### Notes:

1. Package marking provides orientation and identification.
2. See "Electrical Specifications" for appropriate package marking.

#### Description

Hewlett-Packard's HSMS-285L/P and HSMS-286K/L/P/R families have been optimized for use as detectors in the 915 MHz to 5.8 GHz range. The HSMS-285a, with a bandwidth of 0.01 - 7 GHz, requires no battery or power supply, and is well suited as a very simple and inexpensive detector. The HSMS-286a operates in the 0.3 - 8 GHz range and is a high performance detector for upper frequencies.

Available in various package configurations, these two families of detector diodes provide low cost solutions to a wide variety of design problems. Hewlett-Packard's manufacturing techniques assure that when multiple diodes are mounted into a single SOT-363 package, they are taken from adjacent sites on the wafer, assuring the highest possible degree of match.

### DC Electrical Specifications, $T_C = +25^\circ\text{C}$ , Single Diode

Part Number HSMS-	Package Marking Code <sup>[1]</sup>	Lead Code	Configuration	Maximum Forward Voltage $V_F$ (mV)		Typical Capacitance $C_T$ (pF)
285L 285P	PL PP	L P	Unconnected Trio Bridge Quad	150	250	0.30
286K 286L 286P 286R	TK TL TP ZZ	L L P R	High Isolation Unconnected Pair Unconnected Trio Bridge Quad Ring Quad	250	350	0.25
Test Conditions				$I_F = 0.1 \text{ mA}^{[2]}$	$I_F = 1.0 \text{ mA}^{[2]}$	$V_R = 0.5 \text{ V to } -1.0 \text{ V}$ $f = 1 \text{ MHz}^{[3]}$

#### Notes:

1. Package marking code is laser marked.
2.  $\Delta V_F$  for diodes in trios and quads is 15.0 mV maximum at 1.0 mA.
3.  $\Delta C_T$  for diodes in trios and quads is 0.05 pF maximum at -0.5 V.

### RF Electrical Parameters, $T_C = +25^\circ\text{C}$ , Single Diode

Part Number HSMS-	Typical Tangential Sensitivity TSS (dBm) @ f =			Typical Voltage Sensitivity $\gamma$ (mV/ $\mu\text{W}$ ) @ f =			Typical Video Resistance $R_v$ (K $\Omega$ )
	915 MHz	2.45 GHz	5.8 GHz	915 MHz	2.45 GHz	5.8 GHz	
285L 285P	-57	-56	-55	40	30	22	8.0
Test Conditions	Video Bandwidth = 2 MHz Zero Bias			Power in = -40 dBm $R_L = 100 \text{ K}\Omega$ , Zero Bias			Zero Bias
286K 286L 286P 286R	-57	-56	-55	50	35	25	5.0
Test Conditions	Video Bandwidth = 2 MHz $I_b = 5 \mu\text{A}$			Power in = -40 dBm $R_L = 100 \text{ K}\Omega$ , $I_b = 5 \mu\text{A}$			$I_b = 5 \mu\text{A}$

### Absolute Maximum Ratings, $T_C = 25^\circ\text{C}$ , Single Diode

Symbol	Parameter	Unit	Absolute Maximum <sup>[1]</sup>
$P_{IV}$	Peak Inverse Voltage	V	2.0
$T_J$	Junction Temperature	$^\circ\text{C}$	150
$T_{STG}$	Storage Temperature	$^\circ\text{C}$	-65 to 150
$T_{OP}$	Operating Temperature	$^\circ\text{C}$	-65 to 150
$\theta_{jc}$	Thermal Resistance <sup>[2]</sup>	$^\circ\text{C}/\text{W}$	140

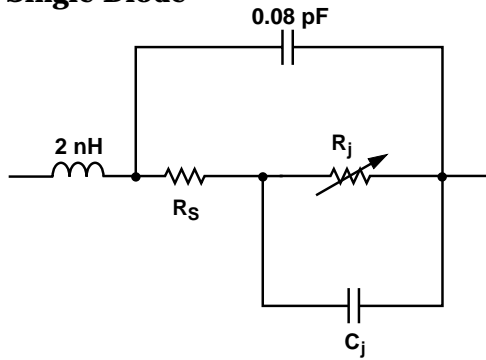
#### ESD WARNING:

Handling Precautions Should Be Taken To Avoid Static Discharge.

#### Notes:

1. Operation in excess of any one of these conditions may result in permanent damage to the device.
2.  $T_C = +25^\circ\text{C}$ , where  $T_C$  is defined to be the temperature at the package pins where contact is made to the circuit board.

### Equivalent Circuit Model HSMS-285 a Series, HSMS-286 a Series Single Diode



$R_S$  = series resistance (see Table of SPICE parameters)

$$R_j = \frac{8.33 \times 10^{-5} \text{ nT}}{I_b + I_s}$$

where

$I_b$  = externally applied bias current in amps

$I_s$  = saturation current (see table of SPICE parameters)

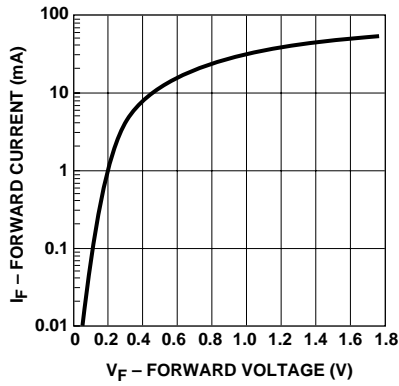
$T$  = temperature, °K

$n$  = ideality factor (see table of SPICE parameters)

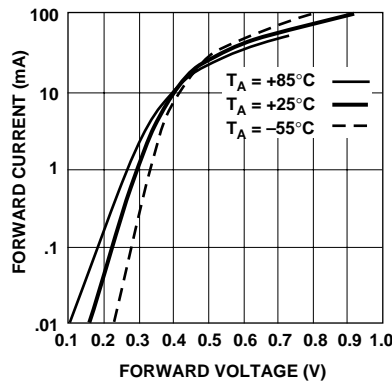
### SPICE Parameters

Parameter	Units	HSMS-285a	HSMS-286a
$B_V$	V	3.8	7.0
$C_{JO}$	pF	0.12	0.10
$E_G$	eV	0.69	0.69
$I_{BV}$	A	3 E-4	1 E-5
$I_S$	A	3 E-6	5 E-8
$N$		1.06	1.08
$R_S$	$\Omega$	30	6.0
$P_B (V_j)$	V	0.35	0.65
$P_T (XTI)$		2	2
$M$		0.5	0.5

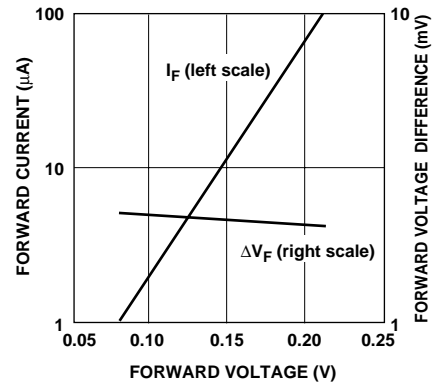
### Typical Parameters, Single Diode



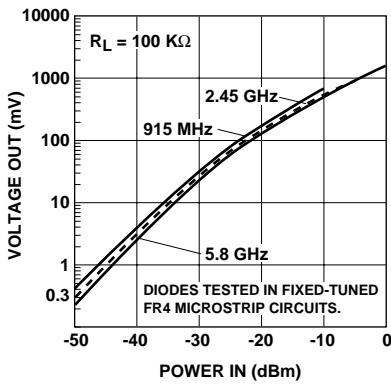
**Figure 1. +25°C Forward Current vs. Forward Voltage, HSMS-285a Series.**



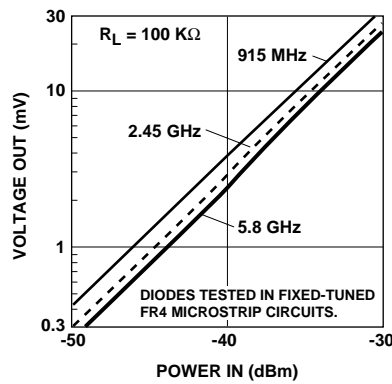
**Figure 2. Forward Current vs. Forward Voltage at Temperature, HSMS-286a Series.**



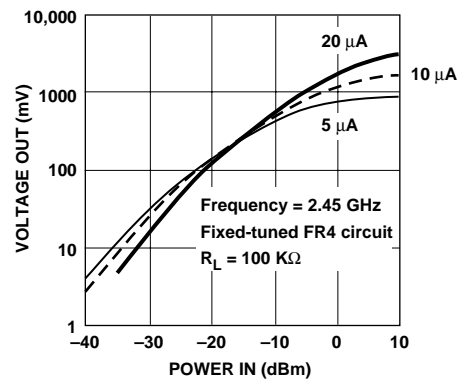
**Figure 3. Forward Voltage Match, HSMS-286a Series.**



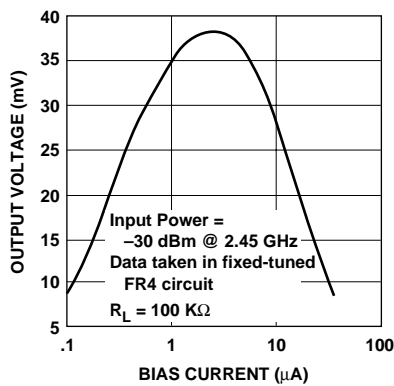
**Figure 4. +25°C Output Voltage vs. Input Power, HSMS-285a Series at Zero Bias, HSMS-286a Series at 3 μA Bias.**



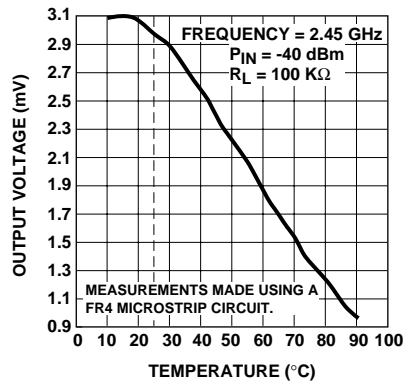
**Figure 5. +25°C Expanded Output Voltage vs. Input Power. See Figure 4.**



**Figure 6. Dynamic Transfer Characteristic as a Function of DC Bias, HSMS-286a.**



**Figure 7. Voltage Sensitivity as a Function of DC Bias Current, HSMS-286a.**



**Figure 8. Output Voltage vs. Temperature, HSMS-285a Series.**

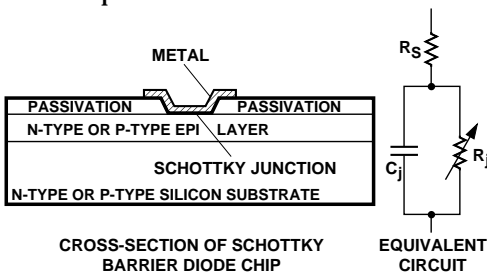
## Applications Information

### Introduction

Hewlett-Packard's HSMS-285L and HSMS-285P zero bias Schottky diodes have been developed specifically for low cost, high volume detector applications where bias current is not available. The HSMS-286L, HSMS-286P and HSMS-286R DC biased Schottky diodes have been developed for low cost, high volume detector applications where stability over temperature is an important design consideration.

### Schottky Barrier Diode Characteristics

Stripped of its package, a Schottky barrier diode chip consists of a metal-semiconductor barrier formed by deposition of a metal layer on a semiconductor. The most common of several different types, the passivated diode, is shown in Figure 9, along with its equivalent circuit.



**Figure 9. Schottky Diode Chip.**

$R_S$  is the parasitic series resistance of the diode, the sum of the bondwire and leadframe resistance, the resistance of the bulk layer of silicon, etc. RF energy coupled into  $R_S$  is lost as heat—it does not contribute to the rectified output of the diode.  $C_J$  is parasitic junction capacitance of the diode, controlled by the thickness of the epitaxial layer and the diameter of the Schottky contact.  $R_J$  is the junction resistance of the diode, a function

of the total current flowing through it.

$$R_J = \frac{8.33 \times 10^{-5} n T}{I_S + I_b} = R_V - R_S$$

$$= \frac{0.026}{I_S + I_b} \text{ at } 25^\circ\text{C}$$

where

$n$  = ideality factor (see table of SPICE parameters)

$T$  = temperature in °K

$I_S$  = saturation current (see table of SPICE parameters)

$I_b$  = externally applied bias current in amps

$I_S$  is a function of diode barrier height, and can range from picoamps for high barrier diodes to as much as 5  $\mu\text{A}$  for very low barrier diodes.

### The Height of the Schottky Barrier

The current-voltage characteristic of a Schottky barrier diode at room temperature is described by the following equation:

$$I = I_S \left( e^{\frac{V - IR_S}{0.026}} - 1 \right)$$

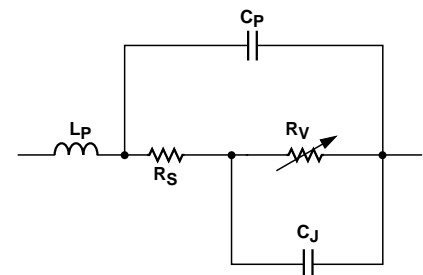
On a semi-log plot (as shown in the HP catalog) the current graph will be a straight line with inverse slope  $2.3 \times 0.026 = 0.060$  volts per cycle (until the effect of  $R_S$  is seen in a curve that droops at high current). All Schottky diode curves have the same slope, but not necessarily the same value of current for a given voltage. This is determined by the saturation current,  $I_S$ , and is related to the barrier height of the diode.

Through the choice of p-type or n-type silicon, and the selection of metal, one can tailor the characteristics of a Schottky diode. Barrier height will be

altered, and at the same time  $C_J$  and  $R_S$  will be changed. In general, very low barrier height diodes (with high values of  $I_S$ , suitable for zero bias applications) are realized on p-type silicon. Such diodes suffer from higher values of  $R_S$  than do the n-type. Thus, p-type diodes are generally reserved for detector applications (where very high values of  $R_V$  swamp out high  $R_S$ ) and n-type diodes are used for mixer applications (where high L.O. drive levels keep  $R_V$  low).

### Measuring Diode Linear Parameters

The measurement of the five elements which make up the equivalent circuit for a packaged Schottky diode (see Figure 10) is a complex task. Various techniques are used for each element. The task begins with the elements of the diode chip itself.



FOR THE HSMS-285A or HSMS-286A SERIES  
 $C_P = 0.08 \text{ pF}$   
 $L_P = 2 \text{ nH}$

**Figure 10. Equivalent Circuit of a Schottky Diode.**

$R_S$  is perhaps the easiest to measure accurately. The V-I curve is measured for the diode under forward bias, and the slope of the curve is taken at some relatively high value of current (such as 5 mA). This slope is converted into a resistance  $R_d$ .

$$R_S = R_d - \frac{0.026}{I_f}$$

$R_V$  and  $C_J$  are very difficult to measure. Consider the impedance of  $C_J = 0.12$  pF when measured at 1 MHz — it is approximately 1 M $\Omega$ . For a well designed zero bias Schottky,  $R_V$  is in the range of 5 to 25 K $\Omega$ , and it shorts out the junction capacitance. Moving up to a higher frequency enables the measurement of the capacitance, but it then shorts out the video resistance. The best measurement technique is to mount the diode in series in a 50  $\Omega$  microstrip test circuit and measure its insertion loss at low power levels (around -20 dBm) using an HP8753C network analyzer. The resulting display will appear as shown in Figure 11.

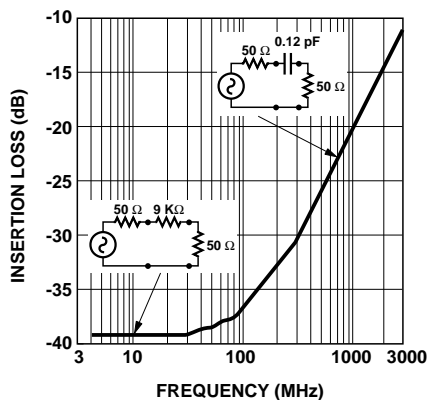


Figure 11. Measuring  $C_J$  and  $R_V$ .

At frequencies below 10 MHz, the video resistance dominates the loss and can easily be calculated from it. At frequencies above 300 MHz, the junction capacitance sets the loss, which plots out as a straight line when frequency is plotted on a log scale. Again, calculation is straightforward.

$L_P$  and  $C_P$  are best measured on the HP8753C, with the diode terminating a 50  $\Omega$  line on the input port. The resulting tabulation of  $S_{11}$  can be put into a microwave linear analysis program having the five element equivalent circuit with  $R_V$ ,  $C_J$  and  $R_S$  fixed. The optimizer can then adjust the values of  $L_P$  and  $C_P$  until the calculated  $S_{11}$  matches the measured values. Note that extreme care must be taken to de-embed the parasitics of the 50  $\Omega$  test fixture.

### Detector Circuits

When DC bias is available, Schottky diode detector circuits can be used to create low cost RF and microwave receivers with a sensitivity of -55 dBm to -57 dBm.<sup>[1]</sup> Moreover, since external DC bias sets the video impedance of such circuits, they display classic square law response over a wide range of input power levels<sup>[2,3]</sup>. These circuits can take a variety of forms, but in the most simple case they appear as shown in Figure 12. This is the basic detector circuit used with the HSMS-286X family of diodes.

Where DC bias is not available, a zero bias Schottky diode is used to replace the conventional Schottky in these circuits, and bias choke  $L_1$  is eliminated. The circuit then is reduced to a diode, an RF impedance matching network and (if required) a DC return choke and a capacitor. This is the basic detector circuit used with the HSMS-285a family of diodes.

Output voltage can be virtually doubled and input impedance (normally very high) can be halved through the use of the voltage doubler circuit<sup>[4]</sup>.

In the design of such detector circuits, the starting point is the equivalent circuit of the diode, as shown in Figure 10. Of interest in the design of the video portion of the circuit is the diode's video impedance — the other four elements of the equivalent circuit disappear at all reasonable video frequencies. In general, the lower the diode's video impedance, the better the design.

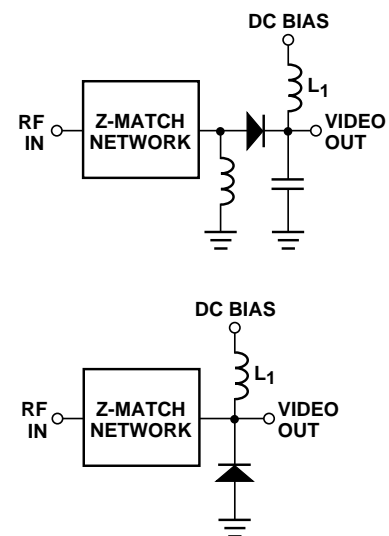


Figure 12. Basic Detector Circuits.

The situation is somewhat more complicated in the design of the RF impedance matching network, which includes the package inductance and capacitance (which can be tuned out), the series resistance, the junction

[1] Hewlett-Packard Application Note 923, *Schottky Barrier Diode Video Detectors*.

[2] Hewlett-Packard Application Note 986, *Square Law and Linear Detection*.

[3] Hewlett-Packard Application Note 956-5, *Dynamic Range Extension of Schottky Detectors*.

[4] Hewlett-Packard Application Note 956-4, *Schottky Diode Voltage Doubler*.

capacitance and the video resistance. Of these five elements of the diode's equivalent circuit, the four parasitics are constants and the video resistance is a function of the current flowing through the diode.

$$R_V \approx \frac{26,000}{I_S + I_b}$$

where

$I_S$  = diode saturation current  
in  $\mu\text{A}$

$I_b$  = bias current in  $\mu\text{A}$

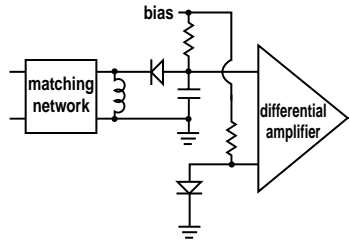
Saturation current is a function of the diode's design,<sup>[5]</sup> and it is a constant at a given temperature. For the HSMS-285X series, it is typically 3 to 5  $\mu\text{A}$  at 25°C. For the medium barrier HSMS-2860 family, saturation current at room temperature is on the order of 50 nA.

Together, saturation and (if used) bias current set the detection sensitivity, video resistance and input RF impedance of the Schottky detector diode. Since no external bias is used with the HSMS-285a series, a single transfer curve at any given frequency is obtained, as shown in Figure 4. Where bias current is used, some tradeoff in sensitivity and square law dynamic range is seen, as shown in Figure 6 and described in reference [3].

The most difficult part of the design of a detector circuit is the input impedance matching network. A discussion of such circuits can be found in the data sheet for the HSMS-285a/HSMS-286a single SOT-323 detector diodes (Hewlett-Packard publication 5965-4704E).

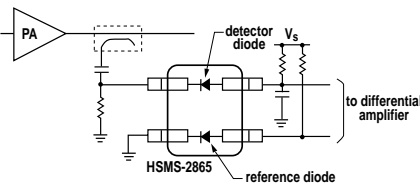
### Six Lead Circuits

The differential detector is often used to provide temperature compensation for a Schottky detector, as shown in Figure 13.



**Figure 13. Differential Detector.**

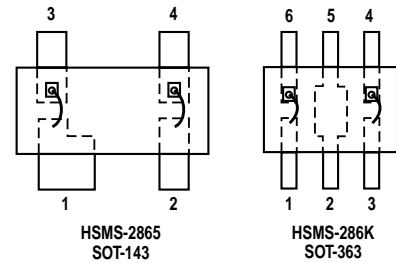
These circuits depend upon the use of two diodes having matched  $V_f$  characteristics over all operating temperatures. This is best achieved by using two diodes in a single package, such as the SOT-143 HSMS-2865 as shown in Figure 14.



**Figure 14. Conventional Differential Detector.**

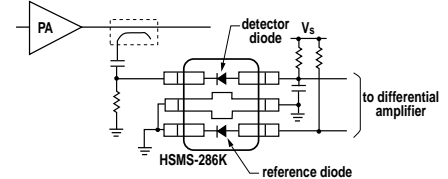
In high power differential detectors, RF coupling from the detector diode to the reference diode produces a rectified voltage in the latter, resulting in errors.

Isolation between the two diodes can be obtained by using the HSMS-286K diode with leads 2 and 5 grounded. The difference between this product and the conventional HSMS-2865 can be seen in Figure 15.



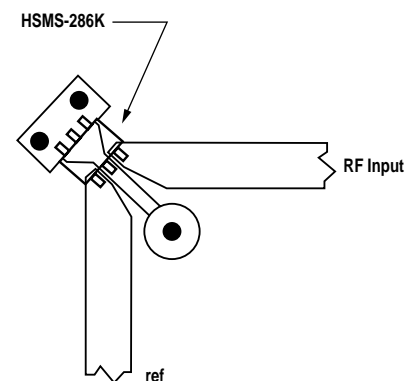
**Figure 15. Comparing Two Diodes.**

The HSMS-286K, with leads 2 and 5 grounded, offers some isolation from RF coupling between the diodes. This product is used in a differential detector as shown in Figure 16.



**Figure 16. High Isolation Differential Detector.**

In order to achieve the maximum isolation, the designer must take care to minimize the distance from leads 2 and 5 and their respective ground via holes. In addition, the ground structure should isolate the input RF and reference lines, as shown in Figure 17.

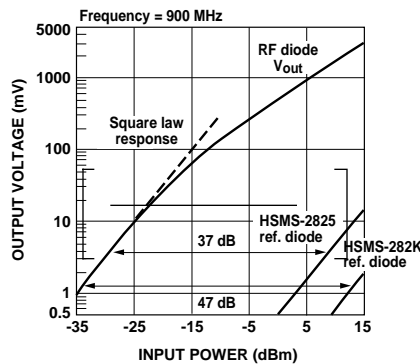


**Figure 17. Diode Mounting, HSMS-286K.**

<sup>[5]</sup> Hewlett-Packard Application Note 969, *An Optimum Zero Bias Schottky Detector Diode*.

Note that the ground strip which runs from the two via holes at the top to the one at the bottom not only provides ground potential for leads 2 and 5, but it isolates the two input/output lines.

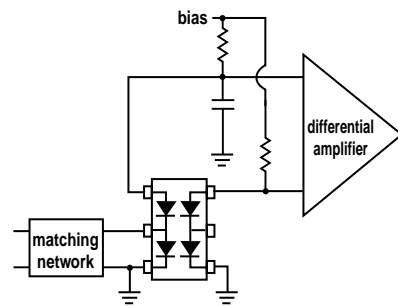
Tests were run on the HSMS-282K and the conventional HSMS-2825 pair, which compare with each other in the same way as the HSMS-2865 and HSMS-286K, with the results shown in Figure 18.



**Figure 18. Comparing HSMS-282K with HSMS-2825.**

The line marked “RF diode,  $V_{out}$ ” is the transfer curve for the detector diode—both the HSMS-2825 and the HSMS-282K exhibited the same output voltage. The data were taken over the 50 dB dynamic range shown. To the right is the output voltage (transfer) curve for the reference diode of the HSMS-2825, showing 37 dB of isolation. To the right of that is the output voltage due to RF leakage for the reference diode of the HSMS-282K, demonstrating 10 dB higher isolation than the conventional part.

Such differential detector circuits generally use single diode detectors, either series or shunt mounted diodes. The voltage doubler (HP Application Note 956-4) offers the advantage of twice the output voltage for a given input power. The two concepts can be combined into the differential voltage doubler, as shown in Figure 19.



**Figure 19. Differential Voltage Doubler, HSMS-286P.**

Here, all four diodes of the HSMS-286P are matched in their  $V_f$  characteristics, because they came from adjacent sites on the wafer. A similar circuit can be realized using the HSMS-286R ring quad.

Other configurations of six lead Schottky products can be used to solve circuit design problems while saving space and cost.

### Thermal Considerations

The obvious advantage of the SOT-363 over the SOT-143 is combination of smaller size and two extra leads. However, the copper leadframe in the SOT-363

has a thermal conductivity four times higher than the Alloy 42 leadframe of the SOT-143, which enables it to dissipate more power.

The maximum junction temperature for these three families of Schottky diodes is 150°C under all operating conditions. The following equation, equation 1, applies to the thermal analysis of diodes:

$$T_j = (V_f I_f + P_{RF}) \theta_{jc} + T_a$$

### Equation (1).

where

$T_j$  = junction temperature

$T_a$  = diode case temperature

$\theta_{jc}$  = thermal resistance

$V_f I_f$  = DC power dissipated

$P_{RF}$  = RF power dissipated

Note that  $\theta_{jc}$ , the thermal resistance from diode junction to the foot of the leads, is the sum of two component resistances,

$$\theta_{jc} = \theta_{pkg} + \theta_{chip}$$

### Equation (2).

Package thermal resistance for the SOT-363 package is approximately 100°C/W, and the chip thermal resistance for these three families of diodes is approximately 40°C/W. The designer will have to add in the thermal resistance from diode case to ambient—a poor choice of circuit board material or heat sink design can make this number very high.



Equation (1) would be straightforward to solve but for the fact that diode forward voltage is a function of temperature as well as forward current. The equation, equation 3, for  $V_f$  is:

$$I_f = I_S \left[ e^{\frac{11600 (V_f - I_f R_s)}{nT}} - 1 \right]$$

**Equation (3).**

where

$n$  = ideality factor

$T$  = temperature in °K

$R_s$  = diode series resistance

and  $I_S$  (diode saturation current) is given by

$$I_s = I_0 \left( \frac{T}{298} \right)^{\frac{2}{n}} e^{-4060 \left( \frac{1}{T} - \frac{1}{298} \right)}$$

**Equation (4).**

Equations (1) and (3) are solved simultaneously to obtain the value of junction temperature for given values of diode case temperature, DC power dissipation and RF power dissipation.

### Temperature Compensation

The compression of the detector's transfer curve is beyond the scope of this data sheet, but some general comments can be made.

As was given earlier, the diode's video resistance is given by

$$R_V = \frac{8.33 \times 10^{-5} nT}{I_S + I_b}$$

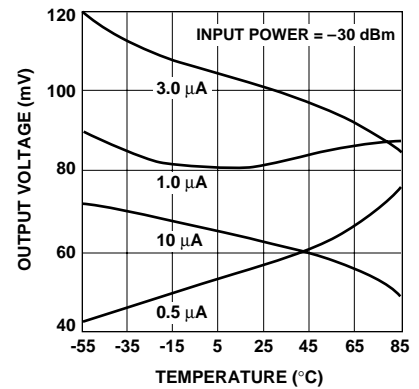
where  $T$  is the diode's temperature in °K.

As can be seen, temperature has a strong effect upon  $R_V$ , and this will in turn affect video bandwidth and input RF impedance. A glance at Figure 7 suggests that the proper choice of bias current in the HSMS-286a series can minimize variation over temperature.

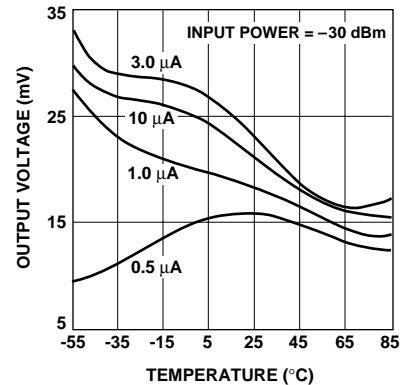
The detector circuits described earlier were tested over temperature. The 915 MHz voltage doubler using the HSMS-286a series produced the output voltages as shown in Figure 20. The use of 3  $\mu$ A of bias resulted in the highest voltage sensitivity, but at the cost of a wide variation over temperature. Dropping the bias to 1  $\mu$ A produced a detector with much less temperature variation.

A similar experiment was conducted with the HSMS-286a series in the 5.8 GHz detector. Once again, reducing the bias to some level under 3  $\mu$ A stabilized the output of the detector over a wide temperature range.

It should be noted that curves such as those given in Figures 20 and 21 are highly dependent upon the exact design of the input impedance matching network. The designer will have to experiment with bias current using his specific design.



**Figure 20. Output Voltage vs. Temperature and Bias Current in the 915 MHz Voltage Doubler using the HSMS-286a Series.**



**Figure 21. Output Voltage vs. Temperature and Bias Current in the 5.80 GHz Voltage Detector using the HSMS-286a Series.**

### Diode Burnout

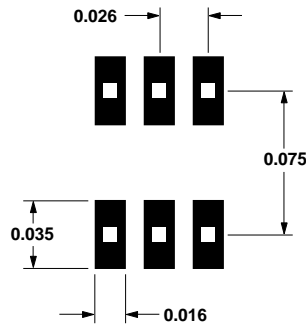
Any Schottky junction, be it an RF diode or the gate of a MESFET, is relatively delicate and can be burned out with excessive RF power. Many crystal video receivers used in RFID (tag) applications find themselves in poorly controlled environments where high power sources may be present. Examples are the areas around airport and FAA radars, nearby ham radio operators, the vicinity of a broadcast band transmitter, etc. In such environments, the Schottky diodes of the receiver can be protected by a device known as a limiter diode.<sup>[6]</sup> Formerly available only in radar warning receivers and other high cost electronic warfare applications, these diodes have been adapted to commercial and consumer circuits.

Hewlett-Packard offers a complete line of surface mountable PIN limiter diodes. Most notably, our HSMP-4820 (SOT-23) or HSMP-482B (SOT-323) can act as a very fast (nanosecond) power-sensitive switch when placed between the antenna and the Schottky diode, shorting out the RF circuit temporarily and reflecting the excessive RF energy back out the antenna.

### Assembly Instructions

#### SOT-363 PCB Footprint

A recommended PCB pad layout for the miniature SOT-363 (SC-70 6 lead) package is shown in Figure 22 (dimensions are in inches). This layout provides ample allowance for package placement by automated assembly equipment without adding parasitics that could impair the performance.



**Figure 22. PCB Pad Layout (dimensions in inches).**

### SMT Assembly

Reliable assembly of surface mount components is a complex process that involves many material, process, and equipment factors, including: method of heating (e.g., IR or vapor phase reflow, wave soldering, etc.) circuit board material, conductor thickness and pattern, type of solder alloy, and the thermal conductivity and thermal mass of components. Components with a low mass, such as the SOT-363 package, will reach solder reflow temperatures faster than those with a greater mass.

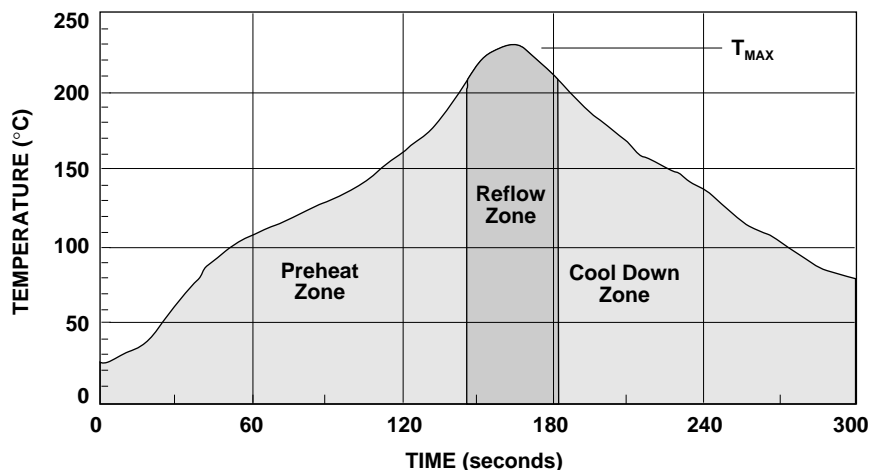
HP's SOT-363 diodes have been qualified to the time-temperature profile shown in Figure 23. This

profile is representative of an IR reflow type of surface mount assembly process.

After ramping up from room temperature, the circuit board with components attached to it (held in place with solder paste) passes through one or more preheat zones. The preheat zones increase the temperature of the board and components to prevent thermal shock and begin evaporating solvents from the solder paste. The reflow zone briefly elevates the temperature sufficiently to produce a reflow of the solder.

The rates of change of temperature for the ramp-up and cool-down zones are chosen to be low enough to not cause deformation of the board or damage to components due to thermal shock. The maximum temperature in the reflow zone ( $T_{MAX}$ ) should not exceed 235 °C.

These parameters are typical for a surface mount assembly process for HP SOT-363 diodes. As a general guideline, the circuit board and components should be exposed only to the minimum temperatures and times necessary to achieve a uniform reflow of solder.

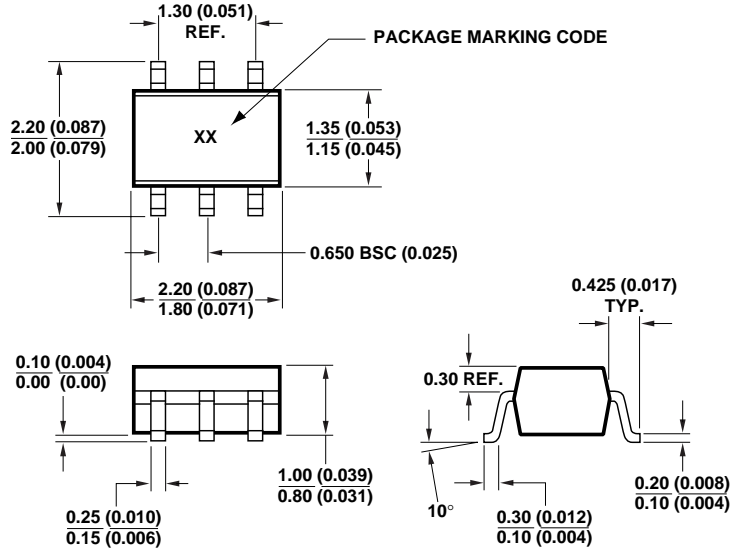


**Figure 23. Surface Mount Assembly Profile.**

<sup>[6]</sup> Hewlett-Packard Application Note 956-4, *Schottky Diode Voltage Doubler*.

## Package Dimensions

### Outline SOT-363 (SC-70, 6 Lead)



DIMENSIONS ARE IN MILLIMETERS (INCHES)

## Part Number Ordering Information

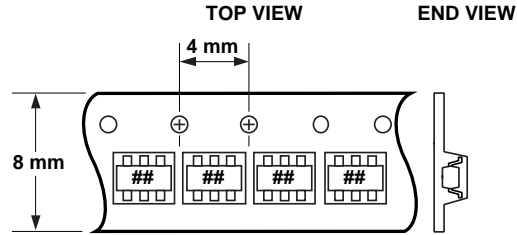
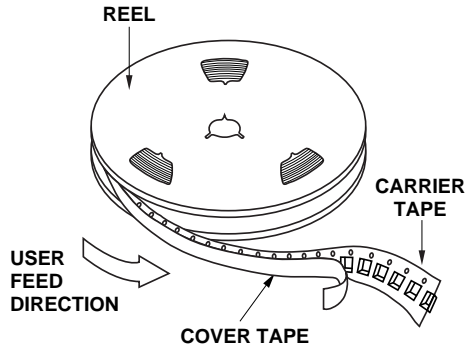
Part Number	No. of Devices	Container
HSMS-28 $x$ a-TR2*	10000	13" Reel
HSMS-28 $x$ a-TR1*	3000	7" Reel
HSMS-28 $x$ a-BLK*	100	antistatic bag

\* where  $x = 5$  or  $6$

$a = L$  or  $P$  for HSMS-285 $a$

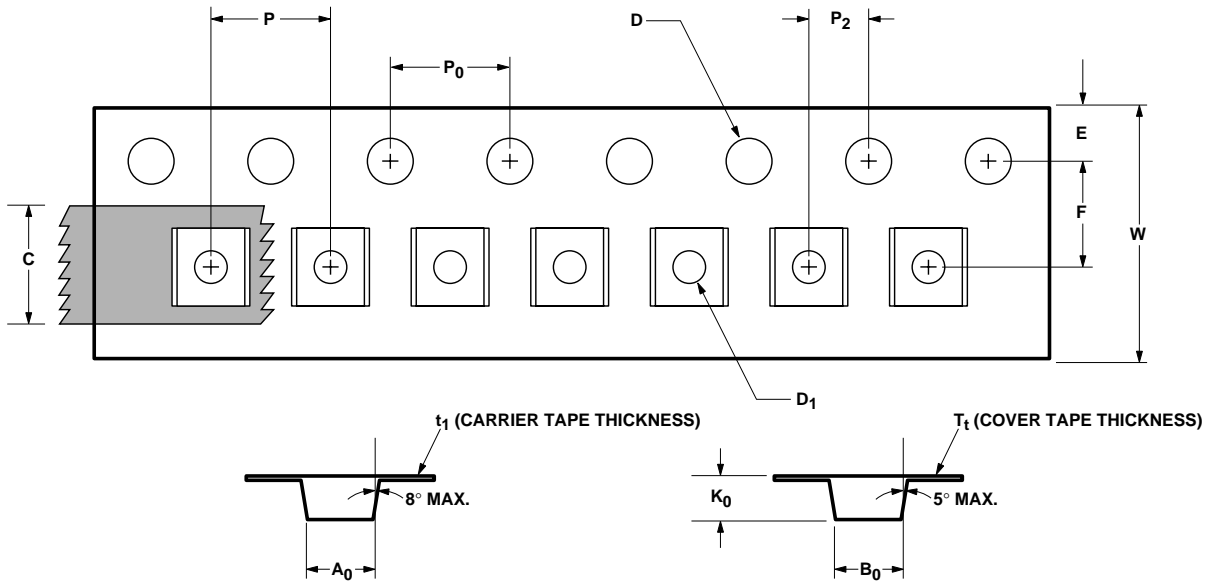
$K, L, P,$  or  $R$  for HSMS-286 $a$

### Device Orientation



Note: “##” represents Package Marking Code. Package marking is right side up with carrier tape perforations at top. Conforms to Electronic Industries RS-481, “Taping of Surface Mounted Components for Automated Placement.” Standard Quantity is 3,000 Devices per Reel.

### Tape Dimensions and Product Orientation For Outline SOT-363 (SC-70, 6 Lead)



DESCRIPTION		SYMBOL	SIZE (mm)	SIZE (INCHES)
CAVITY	LENGTH	A <sub>0</sub>	2.24 ± 0.10	0.088 ± 0.004
	WIDTH	B <sub>0</sub>	2.34 ± 0.10	0.092 ± 0.004
	DEPTH	K <sub>0</sub>	1.22 ± 0.10	0.048 ± 0.004
	PITCH	P	4.00 ± 0.10	0.157 ± 0.004
	BOTTOM HOLE DIAMETER	D <sub>1</sub>	1.00 + 0.25	0.039 + 0.010
PERFORATION	DIAMETER	D	1.55 ± 0.05	0.061 ± 0.002
	PITCH	P <sub>0</sub>	4.00 ± 0.10	0.157 ± 0.004
	POSITION	E	1.75 ± 0.10	0.069 ± 0.004
CARRIER TAPE	WIDTH	W	8.00 ± 0.30	0.315 ± 0.012
	THICKNESS	t <sub>1</sub>	0.255 ± 0.013	0.010 ± 0.0005
COVER TAPE	WIDTH	C	5.4 ± 0.10	0.205 ± 0.004
	TAPE THICKNESS	T <sub>t</sub>	0.062 ± 0.001	0.0025 ± 0.00004
DISTANCE	CAVITY TO PERFORATION (WIDTH DIRECTION)	F	3.50 ± 0.05	0.138 ± 0.002
	CAVITY TO PERFORATION (LENGTH DIRECTION)	P <sub>2</sub>	2.00 ± 0.05	0.079 ± 0.002

[www.hp.com/go/rf](http://www.hp.com/go/rf)

For technical assistance or the location of your nearest Hewlett-Packard sales office, distributor or representative call:

**Americas/Canada:** 1-800-235-0312 or 408-654-8675

**Far East/Australasia:** Call your local HP sales office.

**Japan:** (81 3) 3335-8152

**Europe:** Call your local HP sales office.

Data subject to change.  
Copyright © 1998 Hewlett-Packard Co.

Obsoletes 5966-2032E

5968-2355E (12/98)